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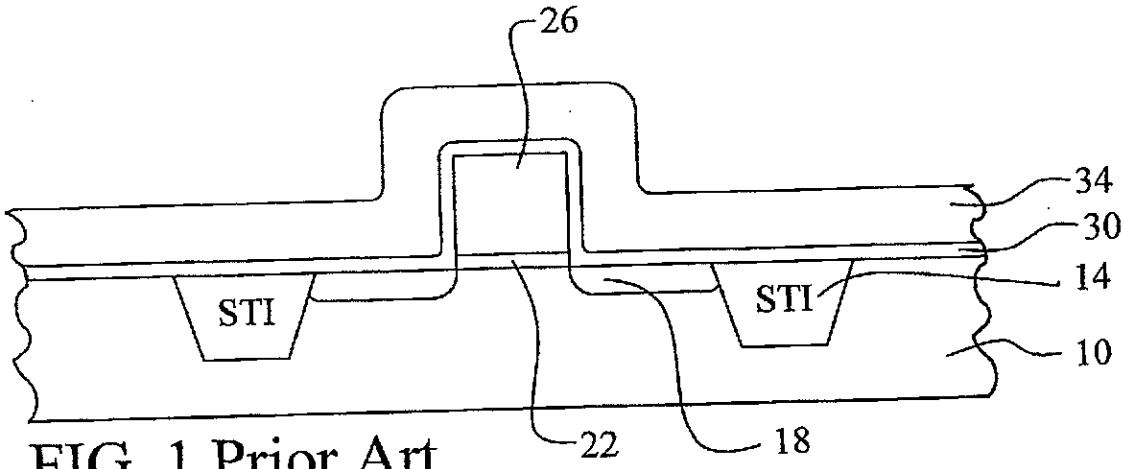



FIG. 1 Prior Art

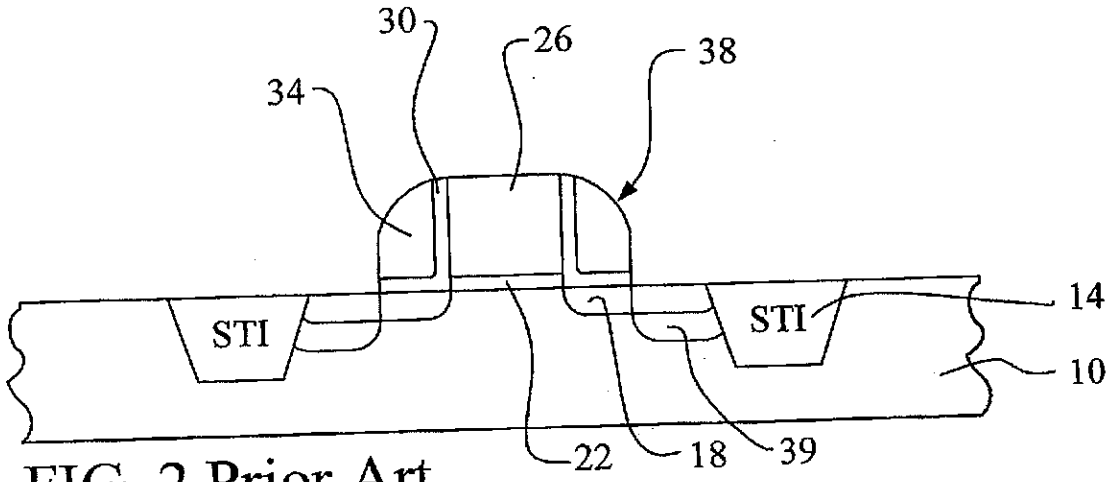



FIG. 2 Prior Art

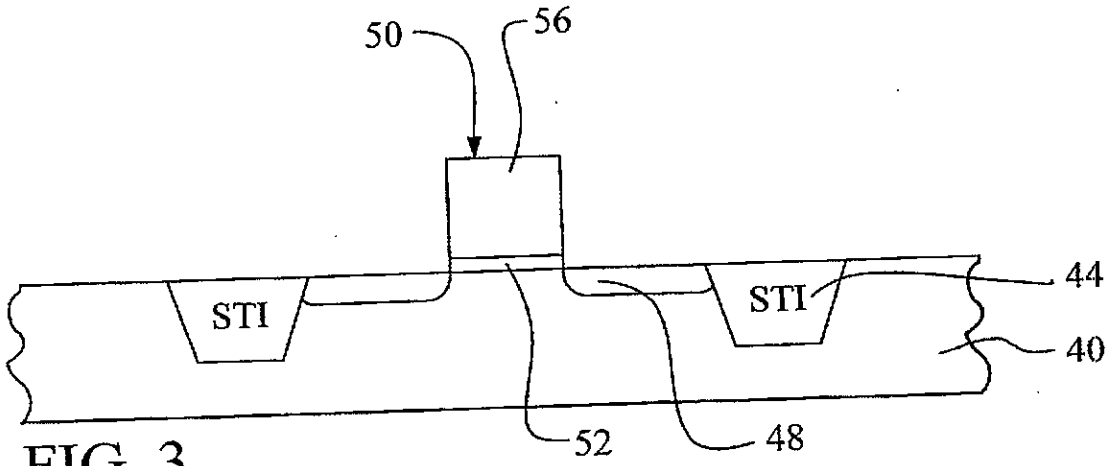



FIG. 3

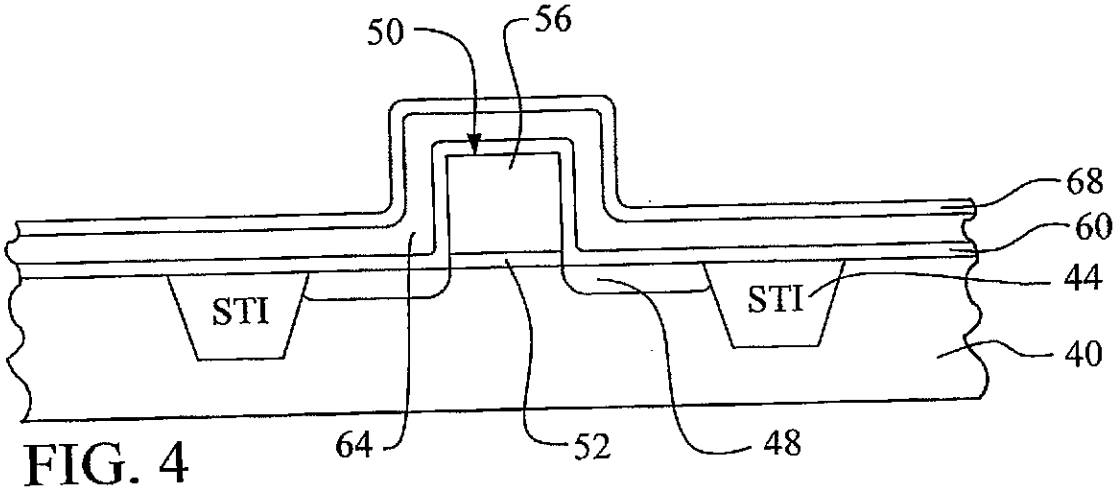

50
56
68
60
44
STI
STI
40
64
52
48

FIG. 4

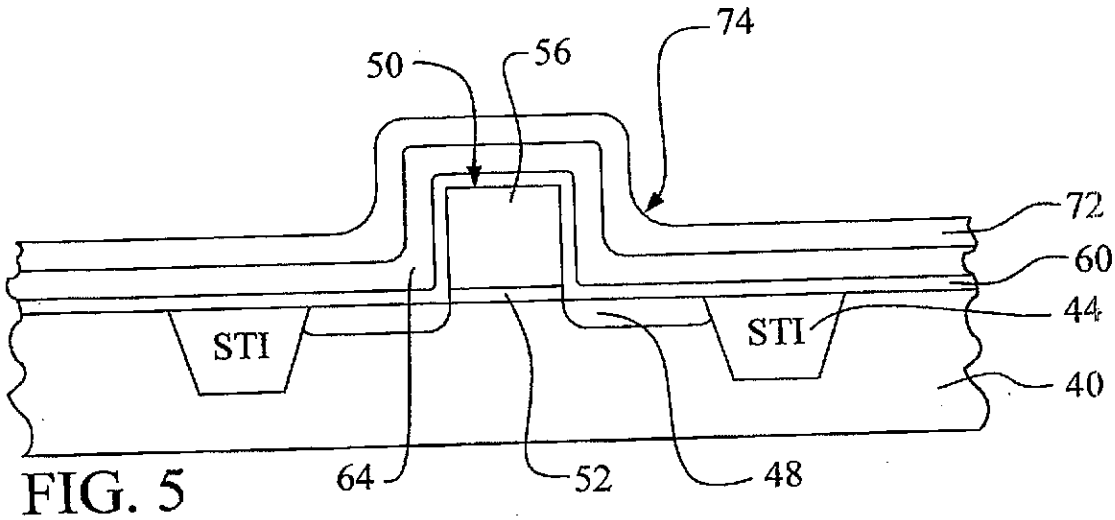

74
50
56
72
60
44
STI
STI
40
64
52
48

FIG. 5

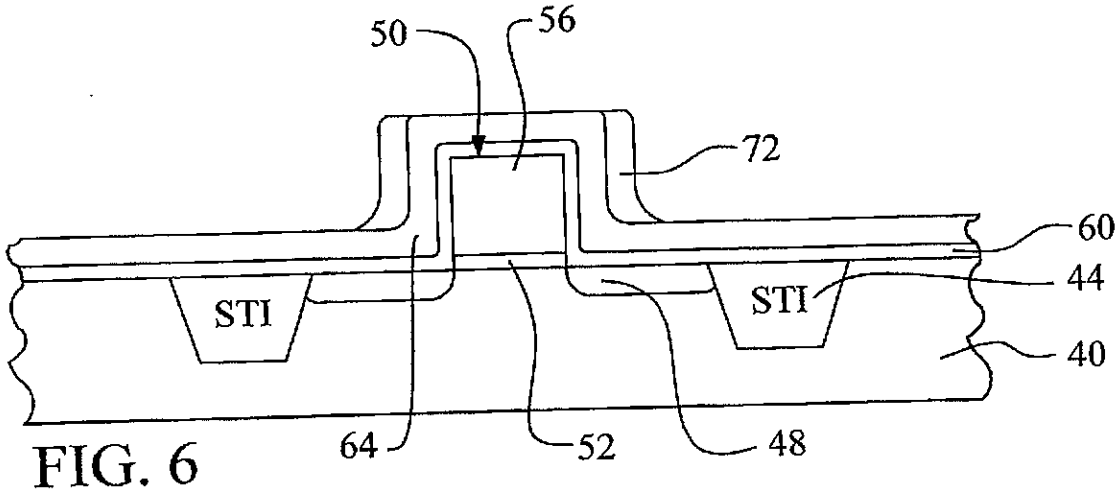



FIG. 6

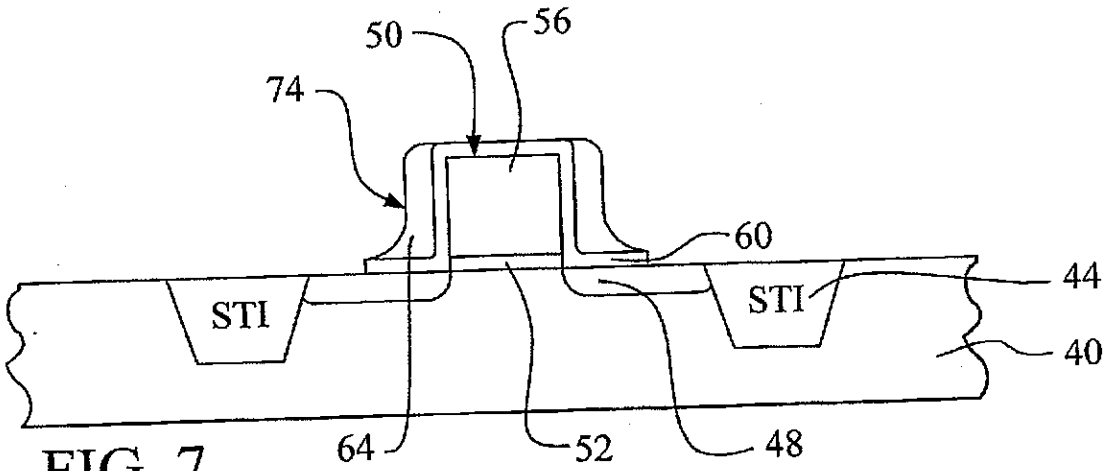



FIG. 7

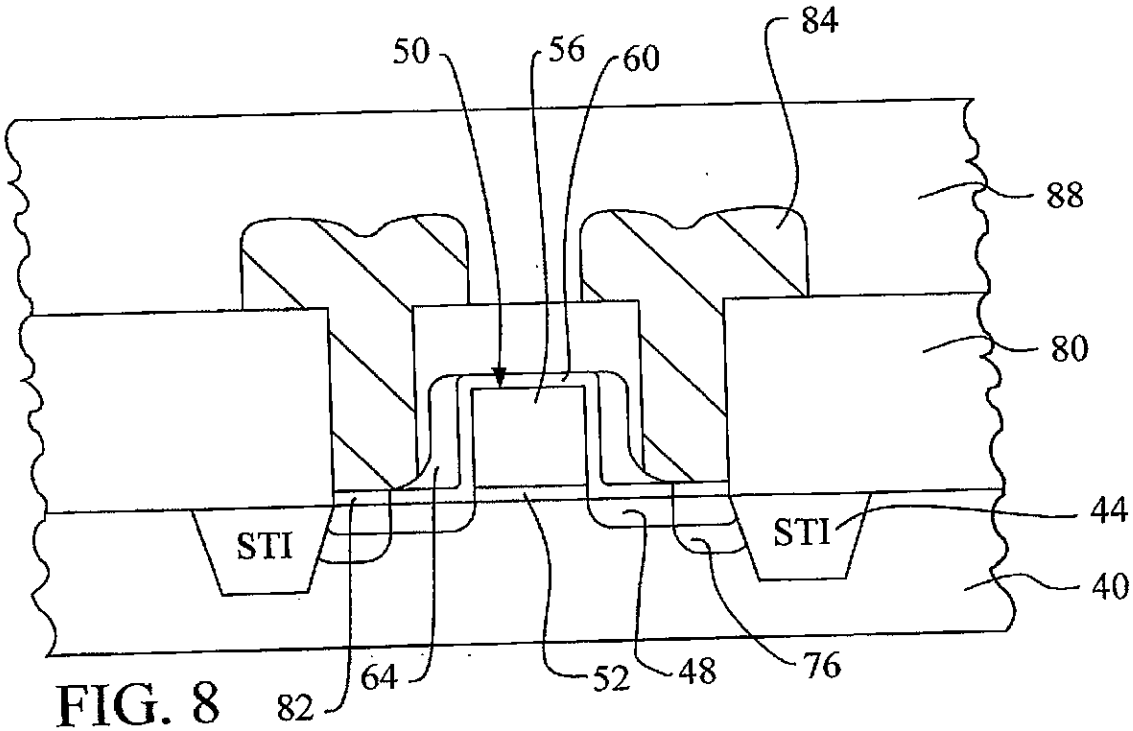

50
56
60
84
88
80
STI
STI
44
40
82
64
52
48
76

FIG. 8

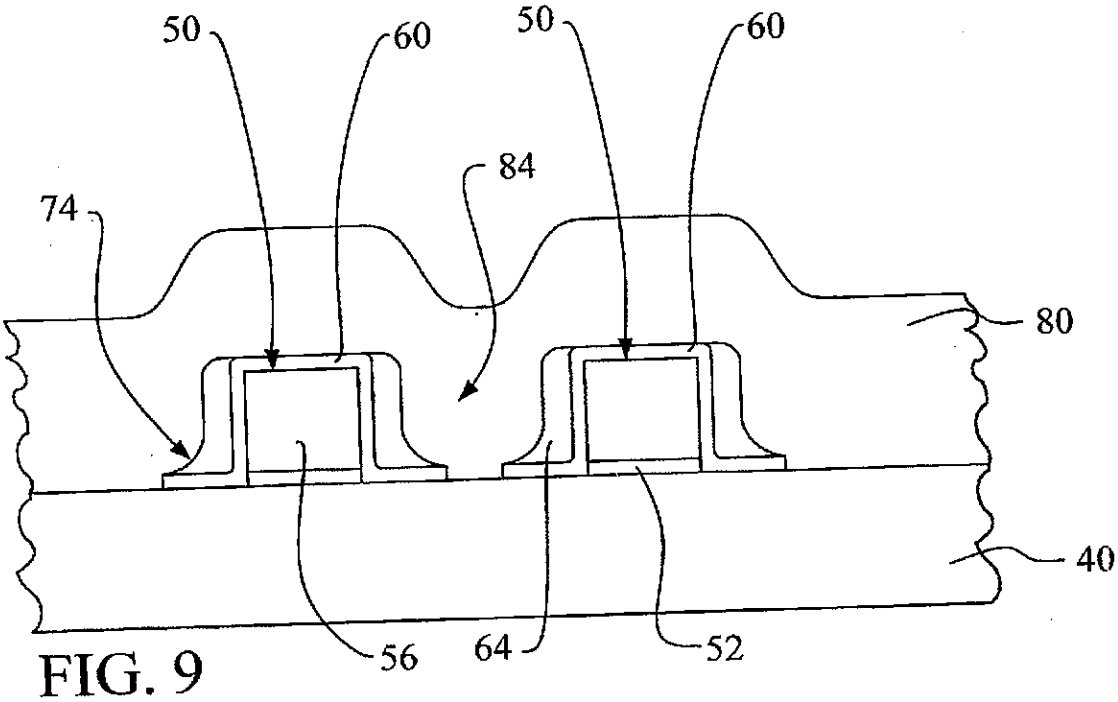

50
60
50
60
84
74
80
40
56
64
52

FIG. 9

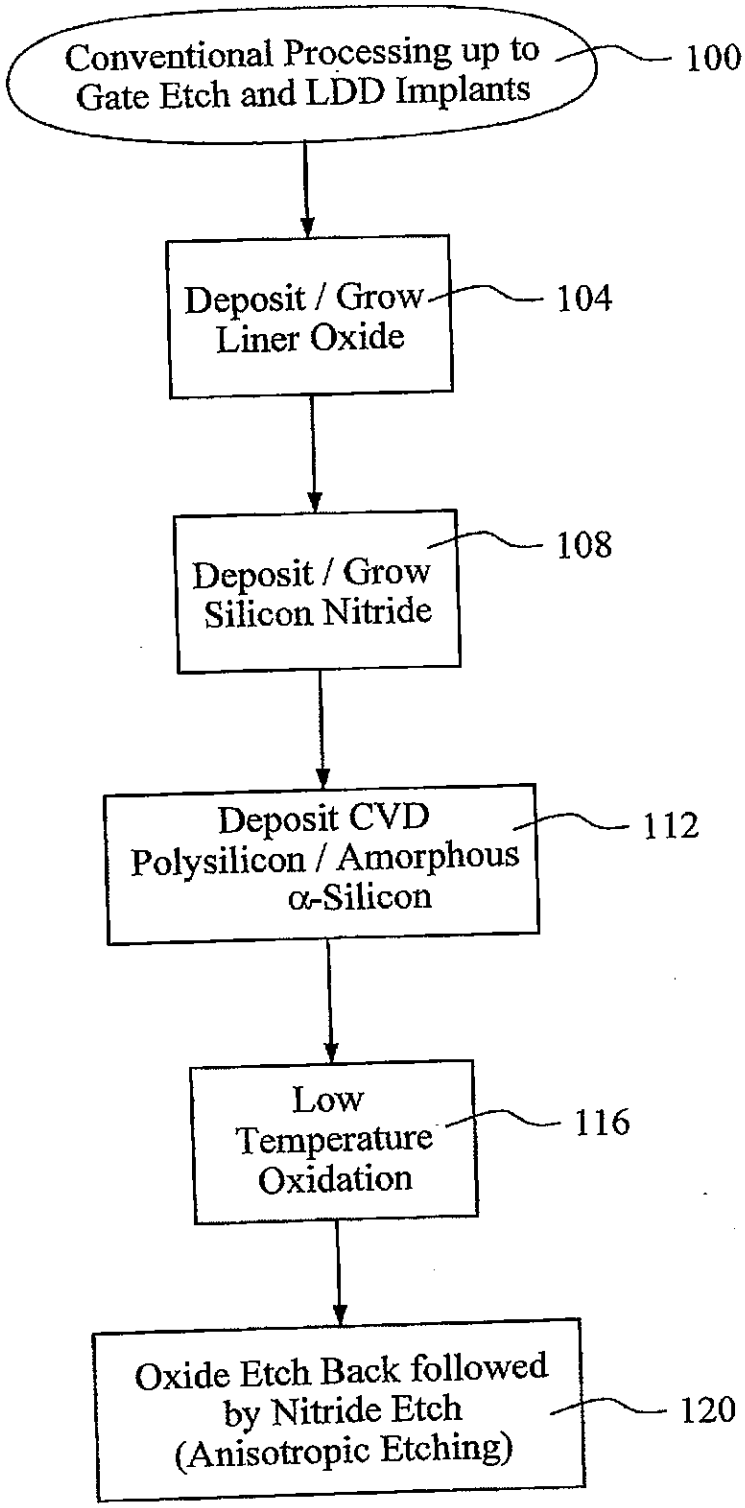

Conventional Processing up to Gate Etch and LDD Implants
100
Deposit / Grow Liner Oxide
104
Deposit / Grow Silicon Nitride
108
Deposit CVD Polysilicon / Amorphous α-Silicon
112
Low Temperature Oxidation
116
Oxide Etch Back followed by Nitride Etch (Anisotropic Etching)
120

FIG. 10